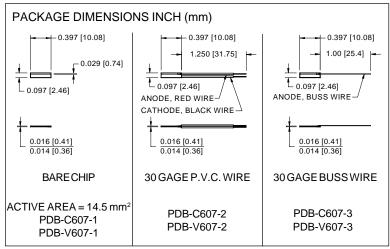
PHOTONIC Silicon Photodiode, Blue Enhanced Solderable Chips

Photoconductive Type PDB-C607 Photovoltaic Type PDB-V607





FEATURES

- Blue enhanced
- Photovoltaic type
- Photoconductive type
- High quantum efficiency

DESCRIPTION: Low cost blue enhanced planar diffused silicon solderable photodiode. The **PDB-V607** cell is designed

for low noise, photovoltaic applications. The PDB-C607 cell is

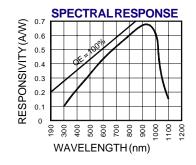
designed for low capacitance, high speed, photoconductive operation. They are available bare, PVC or buss wire leads.

APPLICATIONS

- Optical encoder
- Position sensor
- Industrial controls
- Instrumentation

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER .	PDB-	C607	PDB-	V607	UNITS	
		MIN	MAX	MIN	MAX	Oruito	
VBR	Reverse Voltage		75		25	V	
T _{STG}	Storage Temperature	-40	+125	-40	+125	°C	
То	Operating Temperature Range	-40	+100	-40	+100	°C	
Ts	Soldering Temperature		+224		+224	°C	
I _L	Light Current		500		500	mA	



ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TESTCONDITIONS	PDB-C607			PDB-V607			LINITO
			MIN	TYP	MAX	MIN	TYP	MAX	UNITS
Isc	Short Circuit Current	H = 100 fc, 2850 K	165	185		165	185		μ A
ΙD	Dark Current	H = 0, V _R = 5 V*		15	35		25	50	nA
Rsн	Shunt Resistance	H = 0, V _R = 10 mV	6	15		10	30		MΩ
TC Rsh	RsH Temp. Coefficient	H = 0, V _R = 10 mV		-8			-8		%/°C
CJ	Junction Capacitance	H = 0, V _R = 5 V**		125			2400		pF
λrange	Spectral Application Range	Spot Scan	350		1100	350		1100	nm
λр	Spectral Response - Peak	Spot Scan		940			940		nm
VBR	Breakdown Voltage	I = 10 μA	50	100		5	10		V
NEP	Noise Equivalent Power	V _R = 0 V @ Peak	8 x 10 ⁻¹³ TYP		9 x 10 ⁻¹⁴ TYP			W/ √Hz	
tr	Response Time	RL = 1 KΩ V _R = 5 V**		25			1000		nS

 $^{^*}VR = 100$ mV on Photovoltaic type $^{**}VR = 0$ V on Photovoltaic type